DESCRIPTION

~~SOI WAFER MANUFACTURING METHOD~~

TECHNICAL FIELD

[0001]

The present invention relates to a method for manufacturing an SOI wafer by the ion implantation delamination method.

BACKGROUND ART

[0002]

In manufacture of an SOI wafer by the ion implantation delamination method, when a bond wafer for forming an SOI layer (Silicon On Insulator layer, or Semiconductor On Insulator in a broad sense) and a base wafer are bonded through an oxide film, and then subjected to a heat treatment (a delamination heat treatment) to perform a delamination at an ion-implanted layer, the wafers just after delamination are taken out from a heat treatment furnace with which the delamination heat treatment has been performed in a state that an SOI layer surface (a delaminating plane) of the SOI wafer faces to a surface (a delaminating plane) of the bond wafer (See Patent Document 1, etc.).

[0003]

When a bond wafer on which an oxide film has been formed and a base wafer are bonded to manufacture an SOI wafer, the SOI wafer warps in a convex shape on the delaminating plane side due to a buried oxide film which has been transferred from a surface of the bond wafer by the delamination heat treatment, whereas the bond wafer after delamination warps in a concave shape on the

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